Highly insulated module with Trench/Fieldstop IGBT3 and emitter controlled 3 diode

Features

- Electrical features
  - V_{CES} = 4500 V
  - $I_{C\ nom}$ = 1000 A / I_{CRM} = 2000 A
  - High DC stability
  - High dynamic robustness
  - High short-circuit capability
  - Low $V_{CE,sat}$
  - Trench IGBT 3
  - $V_{CE,sat}$ with positive temperature coefficient
- Mechanical features
  - AlSiC base plate for increased thermal cycling capability
  - High creepage and clearance distances
  - Isolated base plate
  - Package with CTI > 600
  - Package with enhanced insulation of 10.4 kV AC 60 s

Potential applications

- Motor drives
- Traction drives
- Multi-level inverter
- High-power converters
- Medium-voltage converters

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

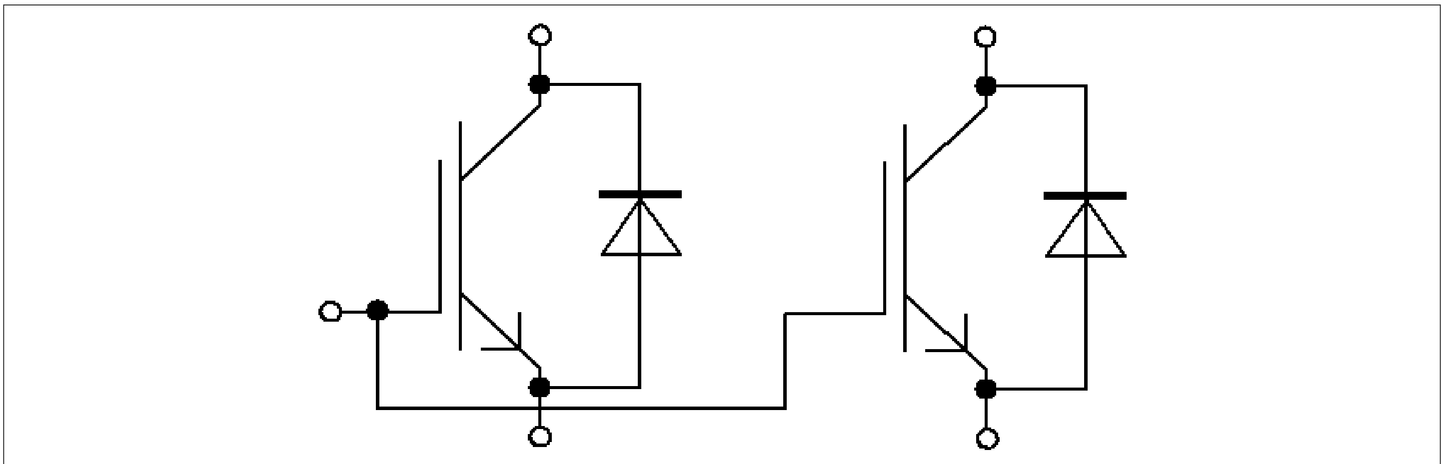


Table of contents

1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f = 50 Hz, t = 60 s	10.4	kV
Partial discharge extinction voltage	V_{isol}	RMS, f = 50 Hz, $Q_{PD} \leq 10$ pC	3.5	kV
DC stability	$V_{CE(D)}$	T_{vj}=25°C, 100 Fit	3000	V
Material of module baseplate			AlSiC	
Internal isolation		basic insulation (class 1, IEC 61140)	AlN	
Creepage distance	d_{Creep}	terminal to heatsink	64.0	mm
Creepage distance	d_{Creep}	terminal to terminal	56.0	mm
Clearance	d_{Clear}	terminal to heatsink	40.0	mm
Clearance	d_{Clear}	terminal to terminal	26.0	mm
Comparative tracking index	CTI		> 600	

Table 2 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Stray inductance module	L_{sCE}				20		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	T_C=25°C, per switch			0.18		mΩ
Storage temperature	T_{stg}			-55		125	°C
Mounting torque for module mounting	M	- Mounting according to valid application note	M6, Screw	4.25		5.75	Nm
Terminal connection torque	M	- Mounting according to valid application note	M4, Screw	1.8		2.1	Nm
			M8, Screw	8		10	
Weight	G				1000		g

Note: The maximum allowed dv/dt measured between 0,6 and 1×Vce is 1400V/µs.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		T_{vj} = -40 °C	4500	V
			T_{vj} = 25 °C	4500	
			T_{vj} = 125 °C	4500	

(table continues...)

Table 3 **(continued) Maximum rated values**

Parameter	Symbol	Note or test condition		Values	Unit
Continuous DC collector current	I_{CDC}	$T_{vj\,max}$ = 150 °C	T_C = 80 °C	1000	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\,op}$		2000	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 4 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\,sat}$	I_C = 1000 A, V_{GE} = 15 V	T_{vj} = 25 °C		2.70	3.05	V
			T_{vj} = 125 °C		3.25	3.85	
Gate threshold voltage	V_{GEth}	I_C = 70.5 mA, V_{CE} = V_{GE}, T_{vj} = 25 °C		5.40	6	6.60	V
Gate charge	Q_G	V_{GE} = ±15 V, V_{CC} = 2800 V			26.5		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			1.1		Ω
Input capacitance	C_{ies}	f = 1000 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			185		nF
Reverse transfer capacitance	C_{res}	f = 1000 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			3.1		nF
Collector-emitter cut-off current	I_{CES}	V_{CE} = 4500 V, V_{GE} = 0 V	T_{vj} = 25 °C			5	mA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25 °C				400	nA
Turn-on delay time (inductive load)	t_{don}	I_C = 1000 A, V_{CC} = 2800 V, V_{GE} = ±15 V, R_{Gon} = 1 Ω	T_{vj} = 25 °C		0.910		µs
			T_{vj} = 125 °C		0.960		
Rise time (inductive load)	t_r	I_C = 1000 A, V_{CC} = 2800 V, V_{GE} = ±15 V, R_{Gon} = 1 Ω	T_{vj} = 25 °C		0.210		µs
			T_{vj} = 125 °C		0.230		
Turn-off delay time (inductive load)	t_{doff}	I_C = 1000 A, V_{CC} = 2800 V, V_{GE} = ±15 V, R_{Goff} = 9.1 Ω	T_{vj} = 25 °C		7.150		µs
			T_{vj} = 125 °C		7.530		
Fall time (inductive load)	t_f	I_C = 1000 A, V_{CC} = 2800 V, V_{GE} = ±15 V, R_{Goff} = 9.1 Ω	T_{vj} = 25 °C		1.100		µs
			T_{vj} = 125 °C		2.120		
Turn-on time (resistive load)	t_{on_R}	I_C = 500 A, V_{CC} = 2000 V, V_{GE} = ±15 V, R_{Gon} = 1 Ω	T_{vj} = 25 °C	1.80			µs
Turn-on energy loss per pulse	E_{on}	I_C = 1000 A, V_{CC} = 2800 V, L_σ = 95 nH, V_{GE} = ±15 V, R_{Gon} = 1 Ω, di/dt = 3500 A/µs (T_{vj} = 125 °C)	T_{vj} = 25 °C		3700		mJ
			T_{vj} = 125 °C		5400		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-off energy loss per pulse	E_{off}	I_C = 1000 A, V_{CC} = 2800 V, L_σ = 95 nH, V_{GE} = ±15 V, R_{Goff} = 9.1 Ω, dv/dt = 1300 V/µs (T_{vj} = 125 °C)	T_{vj} = 25 °C		3800		mJ
			T_{vj} = 125 °C		5000		
SC data	I_{SC}	V_{GE} ≤ 15 V, V_{CC} = 2800 V, $V_{CEmax}=V_{CES}-L_{sCE}$*di/dt	t_P ≤ 10 µs, T_{vj} ≤ 125 °C		4600		A
Thermal resistance, junction to case	R_{thJC}	per IGBT				11.1	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, λ_{grease} = 1 W/(m·K)			13.5		K/kW
Temperature under switching conditions	$T_{vj\,op}$			-50		125	°C

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = -40 °C	4500	V
			T_{vj} = 25 °C	4500	
			T_{vj} = 125 °C	4500	
Continuous DC forward current	I_F			1000	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		2000	A
I^2t - value	I^2t	t_P = 10 ms, V_R = 0 V	T_{vj} = 125 °C	255	kA^2s
Maximum power dissipation	P_{RQM}		T_{vj} = 125 °C	1600	kW
Minimum turn-on time	t_{onmin}			10	µs

Table 6 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 1000 A, V_{GE} = 0 V	T_{vj} = 25 °C		2.80	3.40	V
			T_{vj} = 125 °C		2.70	3.20	
Peak reverse recovery current	I_{RM}	V_{CC} = 2800 V, I_F = 1000 A, V_{GE} = -15 V, -di_F/dt = 3500 A/µs (T_{vj} = 125 °C)	T_{vj} = 25 °C		1030		A
			T_{vj} = 125 °C		1100		

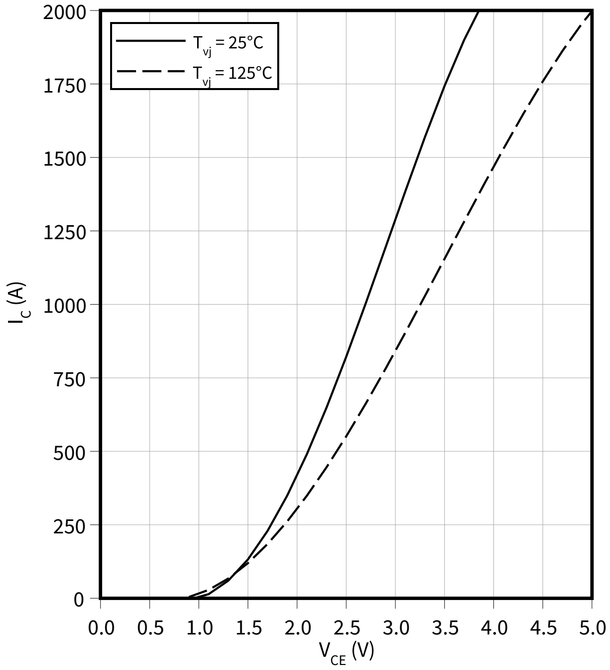
(table continues...)

Table 6 (continued) Characteristic values

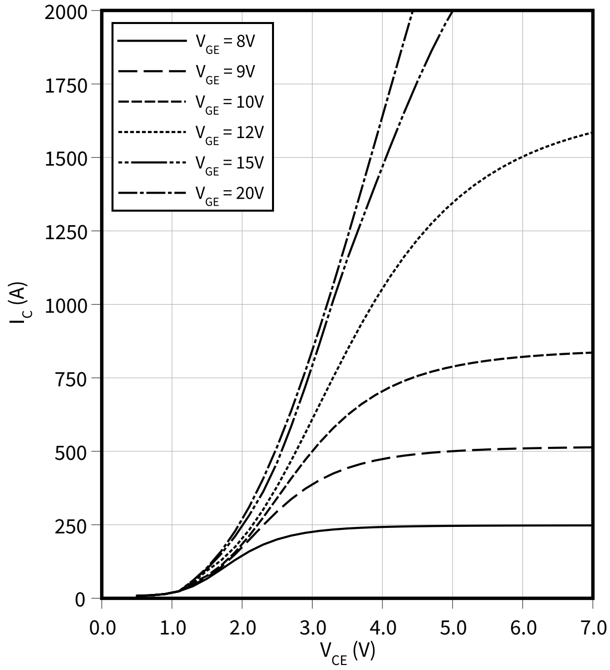
Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Recovered charge	Q_r	V_{CC} = 2800 V, I_F = 1000 A, V_{GE} = -15 V, -di$_F$/dt = 3500 A/µs (T_{vj} = 125 °C)	T_{vj} = 25 °C		860		µC
			T_{vj} = 125 °C		1700		
Reverse recovery energy	E_{rec}	V_{CC} = 2800 V, I_F = 1000 A, V_{GE} = -15 V, -di$_F$/dt = 3500 A/µs (T_{vj} = 125 °C)	T_{vj} = 25 °C		1300		mJ
			T_{vj} = 125 °C		2800		
Thermal resistance, junction to case	R_{thJC}	per diode				25.5	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per diode, λ_{grease} = 1 W/(m·K)			21.0		K/kW
Temperature under switching conditions	$T_{vj\,op}$			-50		125	°C

4 Characteristics diagrams

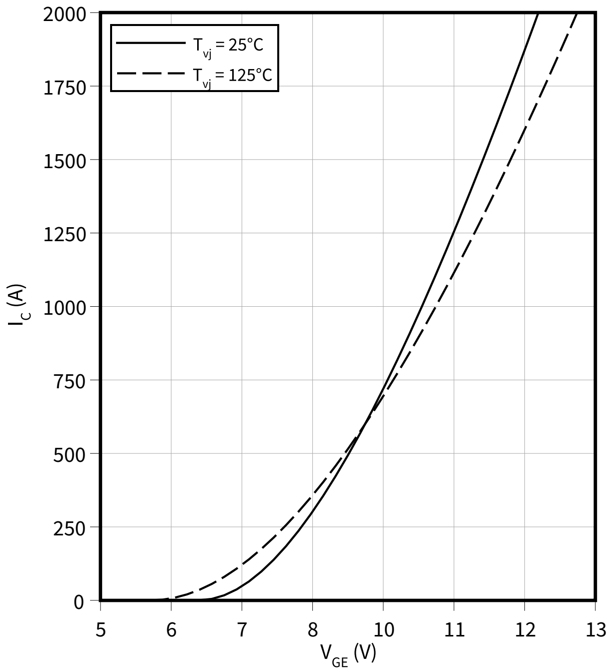
Output characteristic (typical), IGBT, Inverter
$I_C = f(V_{CE})$
$V_{GE} = 15\ V$



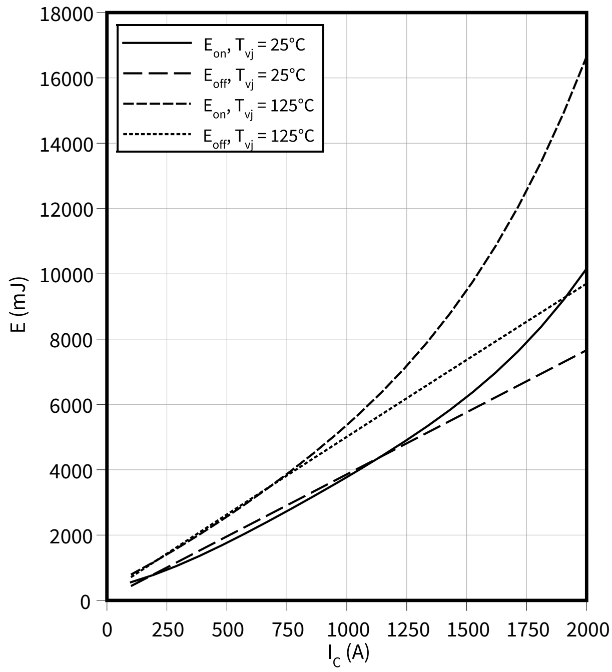
Output characteristic field (typical), IGBT, Inverter
$I_C = f(V_{CE})$
$T_{vj} = 125\ °C$



Transfer characteristic (typical), IGBT, Inverter
$I_C = f(V_{GE})$
$V_{CE} = 20\ V$



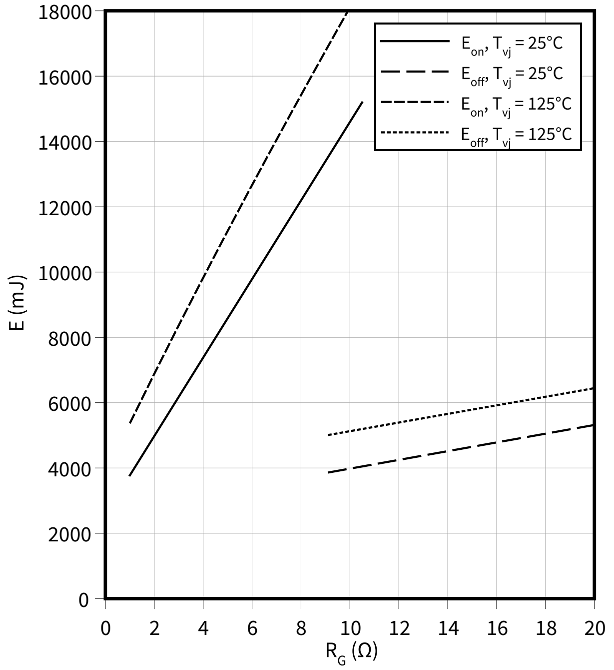
Switching losses (typical), IGBT, Inverter
$E = f(I_C)$
$R_{Goff} = 9{,}1\ \Omega$, $R_{Gon} = 1\ \Omega$, $V_{CC} = 2800\ V$, $V_{GE} = \pm 15\ V$



Switching losses (typical), IGBT, Inverter

$E = f(R_G)$

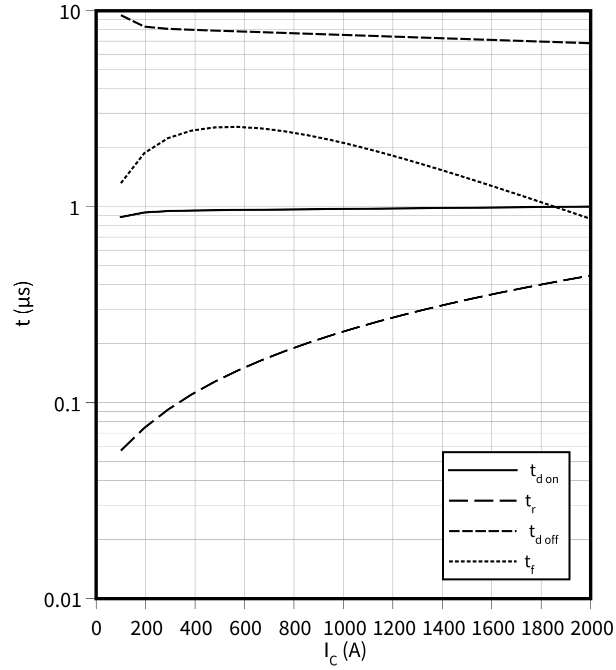
I_C = 1000 A, V_{CC} = 2800 V, V_{GE} = ± 15 V



Switching times (typical), IGBT, Inverter

$t = f(I_C)$

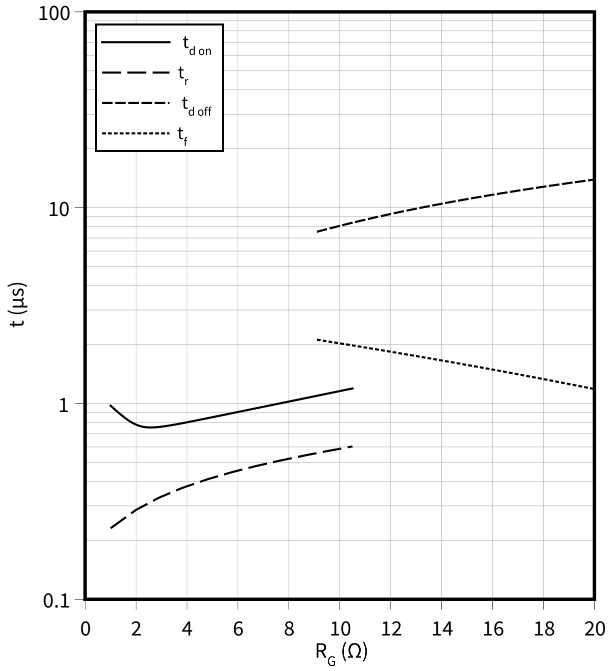
R_{Goff} = 9.1 Ω, R_{Gon} = 1 Ω, V_{GE} = ±15 V, V_{CC} = 2800 V, T_{vj} = 125 °C



Switching times (typical), IGBT, Inverter

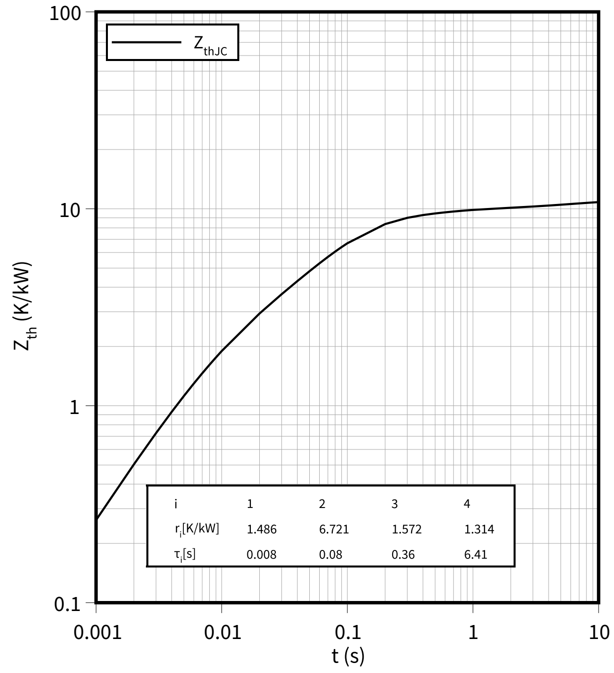
$t = f(R_G)$

V_{GE} = ±15 V, I_C = 1000 A, V_{CC} = 2800 V, T_{vj} = 125 °C



Transient thermal impedance , IGBT, Inverter

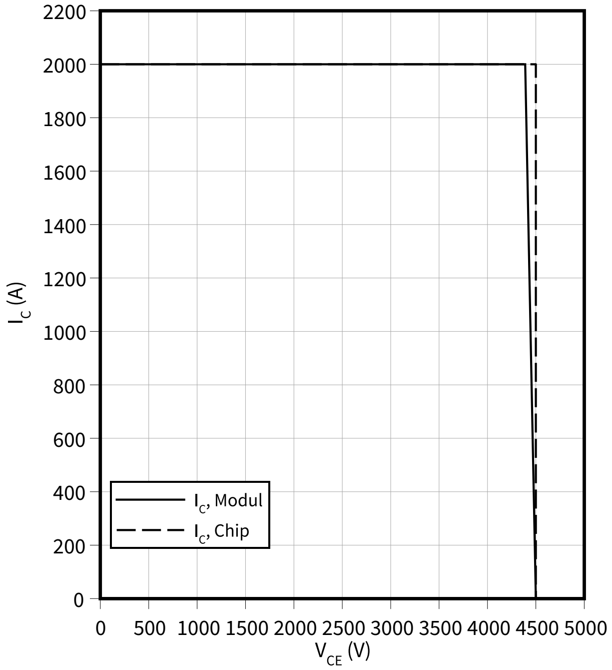
$Z_{th} = f(t)$



Reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$

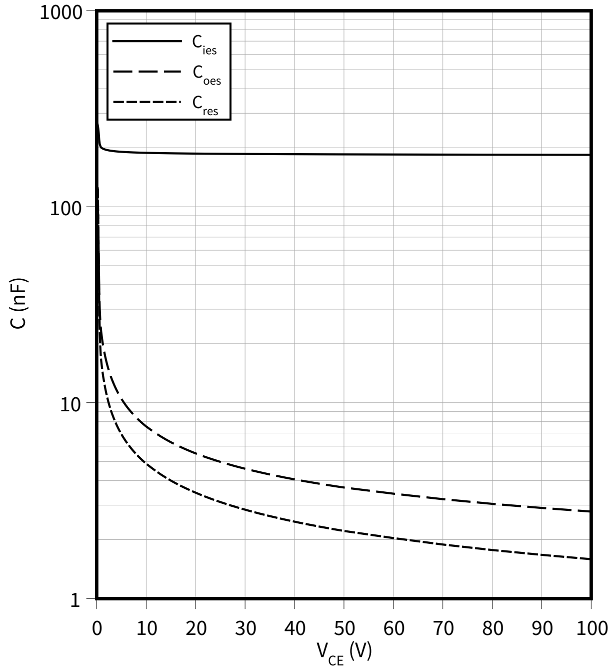
$R_{Goff} = 9.1\ \Omega$, $V_{GE} = \pm 15$ V, $T_{vj} = 125$ °C



Capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$

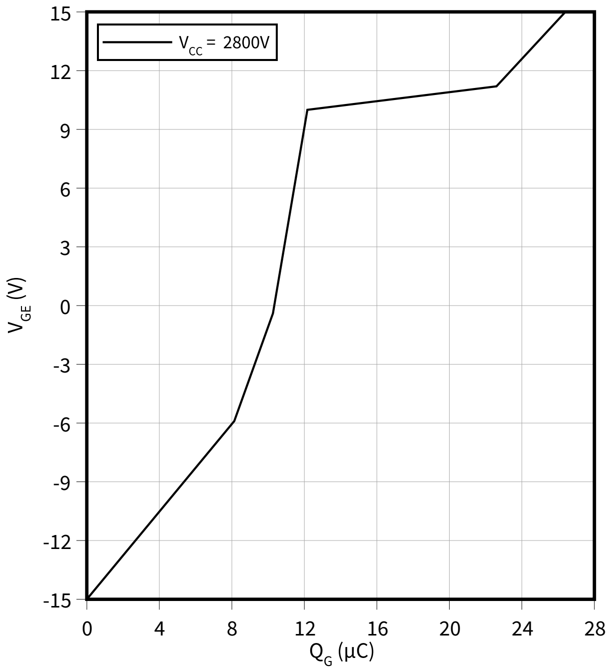
$f = 1000$ kHz, $V_{GE} = 0$ V, $T_{vj} = 25$ °C



Gate charge characteristic (typical), IGBT, Inverter

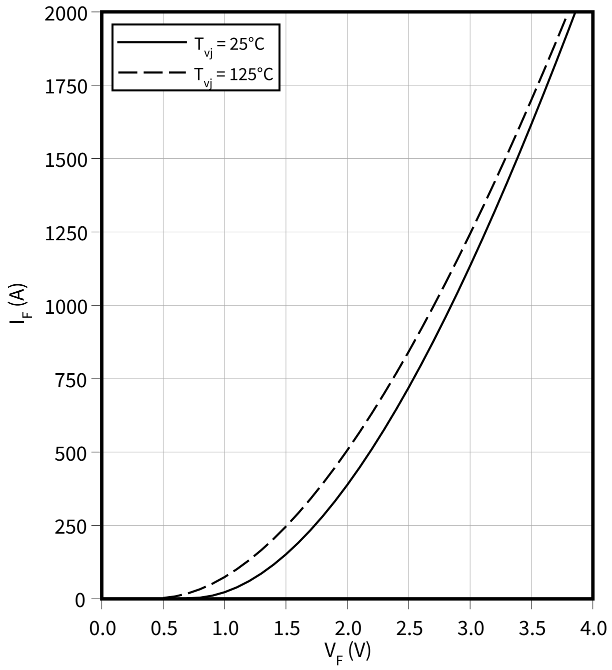
$V_{GE} = f(Q_G)$

$I_C = 1000$ A, $T_{vj} = 25$ °C



Forward characteristic (typical), Diode, Inverter

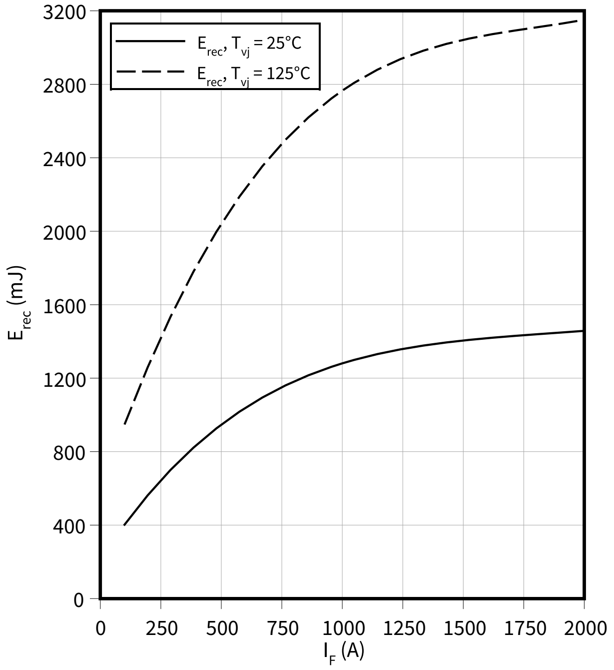
$I_F = f(V_F)$



Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

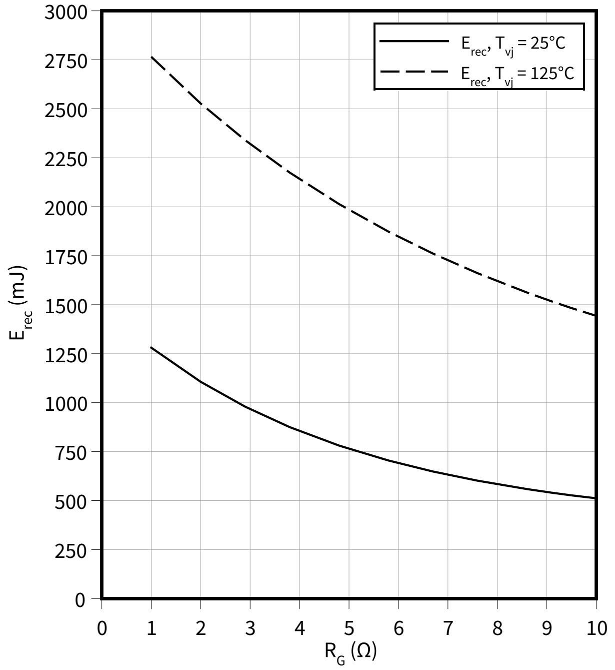
$R_{Gon} = R_{Gon}(IGBT)$, $V_{CC} = 2800$ V



Switching losses (typical), Diode, Inverter

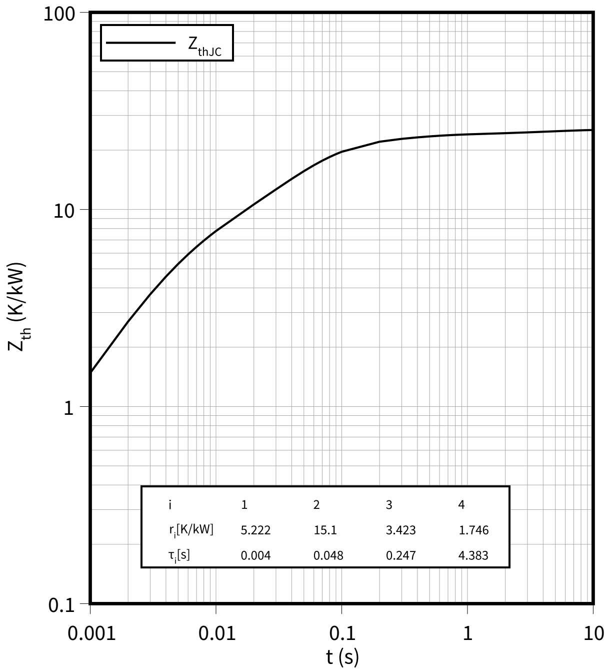
$E_{rec} = f(R_G)$

$I_F = 1000$ A, $V_{CC} = 2800$ V



Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$

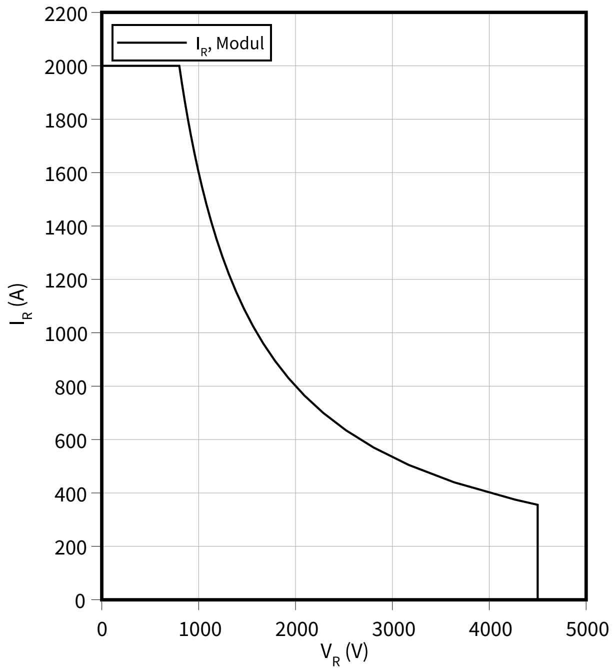


i	1	2	3	4
r_i[K/kW]	5.222	15.1	3.423	1.746
τ_i[s]	0.004	0.048	0.247	4.383

Safe operating area (SOA), Diode, Inverter

$I_R = f(V_R)$

$T_{vj} = 125$ °C



5 Circuit diagram

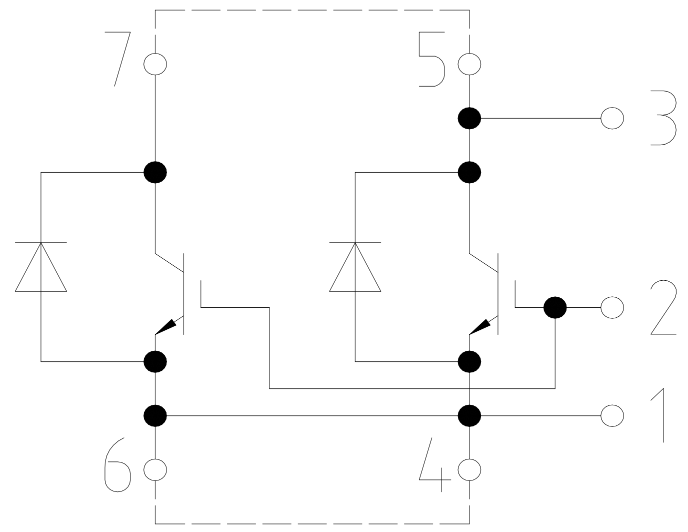


Figure 1

6 Package outlines

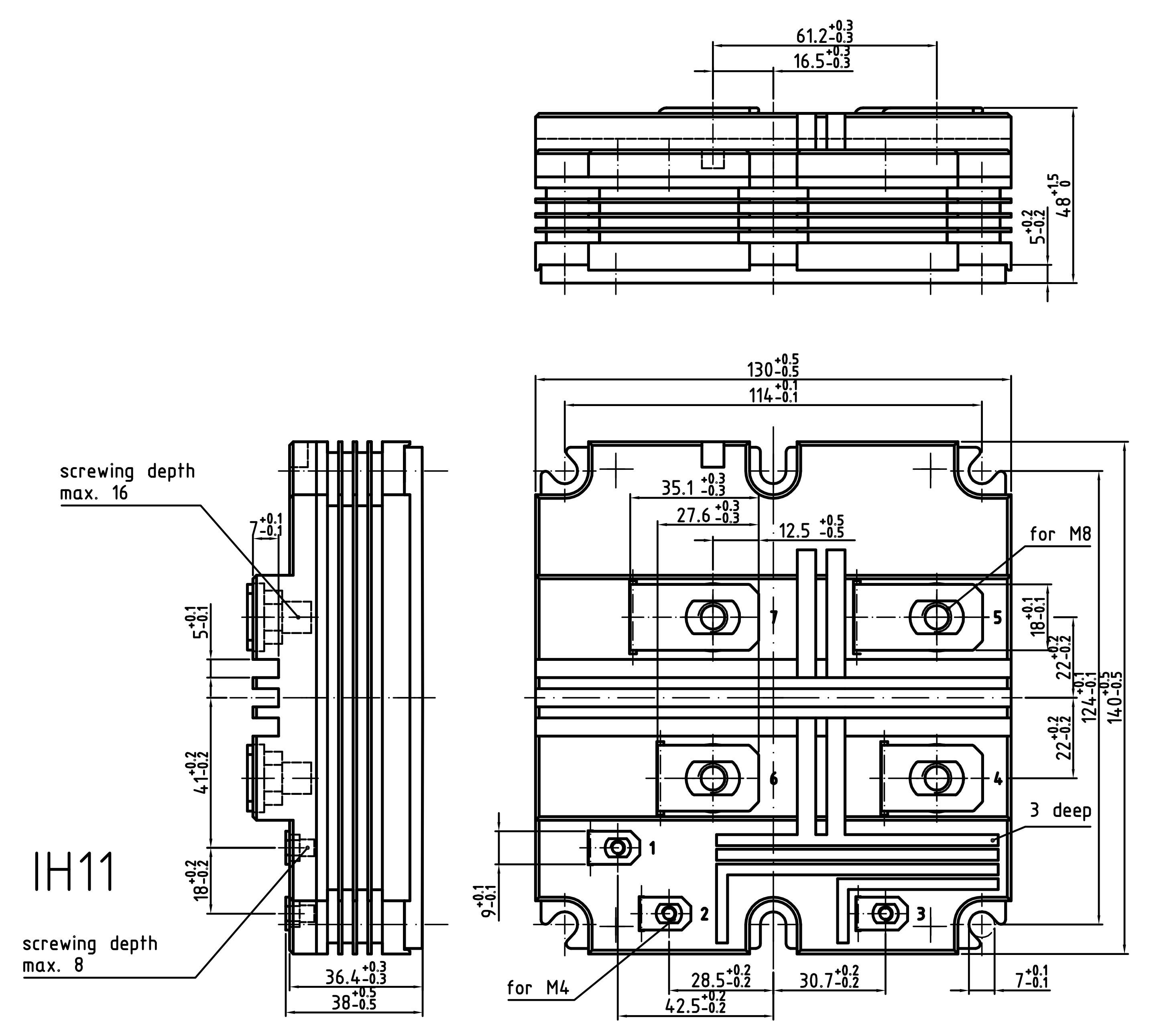


Figure 2

7 Module label code

Module label code		
Code format	Data Matrix	Barcode Code128
Encoding	ASCII text	Code Set A
Symbol size	16x16	23 digits
Standard	IEC24720 and IEC16022	IEC8859-1

Code content	*Content* Module serial number Module material number Production order number Date code (production year) Date code (production week)	*Digit* 1 – 5 6 - 11 12 - 19 20 – 21 22 – 23	*Example* 71549 142846 55054991 15 30
Example	71549142846550549911530	71549142846550549911530	

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2021-09-15	Initial version
0.20	2022-02-24	Target datasheet
0.30	2022-05-16	Preliminary datasheet
1.00	2022-08-15	Final datasheet

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Edition 2022-08-15

Published by

Infineon Technologies AG

81726 Munich, Germany

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Document reference
IFX-ABA154-004

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